

Features

- New Thin Wafer Technology
- Low Forward Voltage Drop (V_F)
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- Temperature-independent Switching
- Positive Temperature Coefficient on V_F
- Compliant to Halogen-free

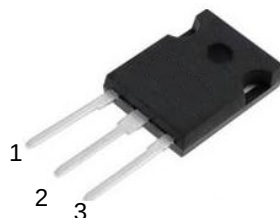
V_{RRM}	=	1200	V
$I_F (T_C \leq 135^\circ\text{C})$	=	48	A**
Q_C	=	100	nC**

*Per Leg, **Per Device

Benefits

- Replace Bipolar with Unipolar Device
- Reduction of Heat Sink Size
- Parallel Devices Without Thermal Runaway
- Essentially No Switching Losses

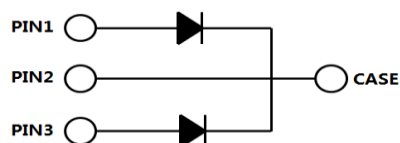
Package



TO-247-3

Applications

- Switch mode power supplies (SMPS)
- Uninterruptible power supplies
- Motor drive, PV Inverter, Wind Power Station



Part Number	Package	Marking
AS4D040120P2	TO-247-3	AS4D040120P2

Maximum Ratings

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V	$T_C = 25^{\circ}\text{C}$	
V_{RSM}	Surge Peak Reverse Voltage	1200	V	$T_C = 25^{\circ}\text{C}$	
V_R	DC Blocking Voltage	1200	V	$T_C = 25^{\circ}\text{C}$	
I_F	Forward Current (Per leg/Device)	40/80 24/48 20/40	A	$T_C \leq 25^{\circ}\text{C}$ $T_C \leq 135^{\circ}\text{C}$ $T_C \leq 145^{\circ}\text{C}$	
I_{FSM}	Non-Repetitive Forward Surge Current	180*	A	$T_C = 25^{\circ}\text{C}$, $t_p = 8.3\text{ms}$, Half Sine Wave	
P_{tot}	Power Dissipation(Per leg/Device)	214/428	W	$T_C = 25^{\circ}\text{C}$	Fig.3
T_J, T_{STG}	Operating Junction and Storage Temperature	-55 to 175	$^{\circ}\text{C}$		
	TO-247 Mounting Torque	1	Nm	M3 Screw	

*Per Leg, **Per Device

Electrical Characteristics (Per leg)

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.45 2.0	1.8 /	V	$I_F = 20\text{A}$, $T_J = 25^{\circ}\text{C}$ $I_F = 20\text{A}$, $T_J = 175^{\circ}\text{C}$	Fig.1
I_R	Reverse Current	10 50	100 500	μA	$V_R = 1200\text{V}$, $T_J = 25^{\circ}\text{C}$ $V_R = 1200\text{V}$, $T_J = 175^{\circ}\text{C}$	Fig.2
C	Total Capacitance	1220 87 64	/	pF	$V_R = 0.1\text{V}$, $T_J = 25^{\circ}\text{C}$, $f = 1\text{MHz}$ $V_R = 400\text{V}$, $T_J = 25^{\circ}\text{C}$, $f = 1\text{MHz}$ $V_R = 800\text{V}$, $T_J = 25^{\circ}\text{C}$, $f = 1\text{MHz}$	Fig.5
Q_C	Total Capacitive Charge	50	/	nC	$V_R = 800\text{V}$, $I_F = 20\text{A}$ $di/dt = 200\text{A}/\mu\text{s}$, $T_J = 25^{\circ}\text{C}$	Fig.4

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.7* 0.35**	$^{\circ}\text{C}/\text{W}$	Fig.6
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	80	$^{\circ}\text{C}/\text{W}$	
T_{sld}	Soldering Temperature	260	$^{\circ}\text{C}$	

*Per Leg, **Per Device

Typical Performance (Per Leg)

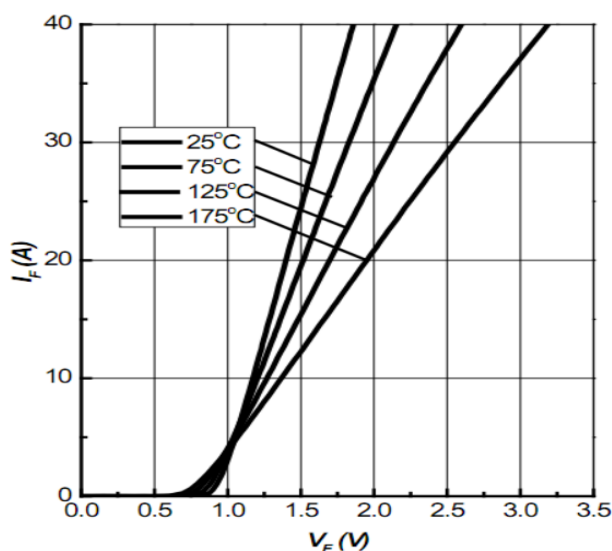


Figure 1. Forward Characteristics

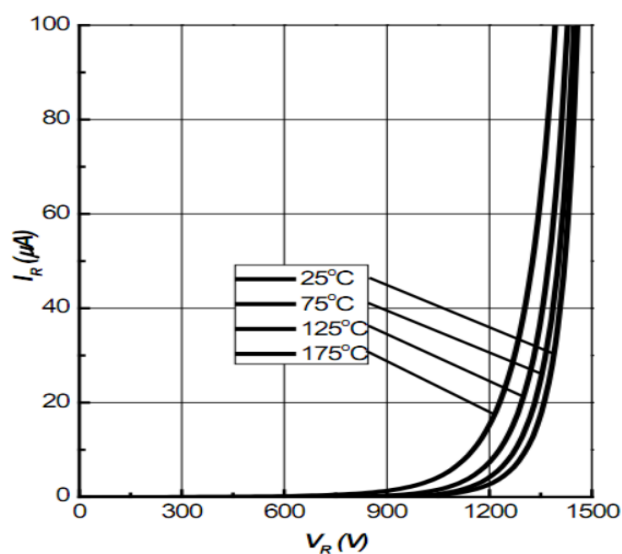


Figure 2. Reverse Characteristics

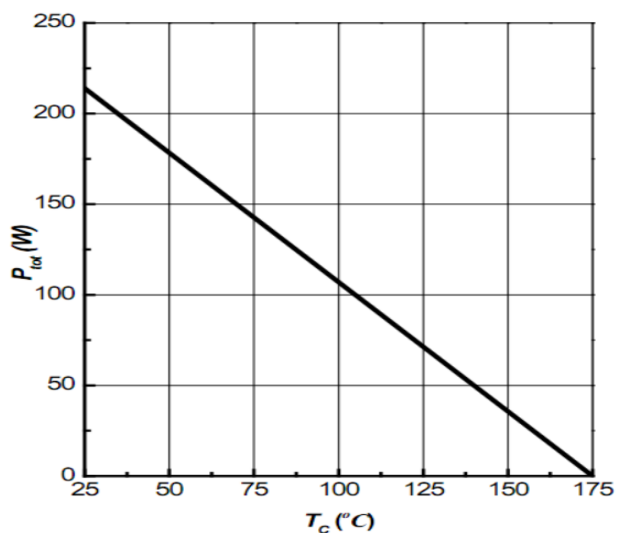


Figure 3. Power Derating

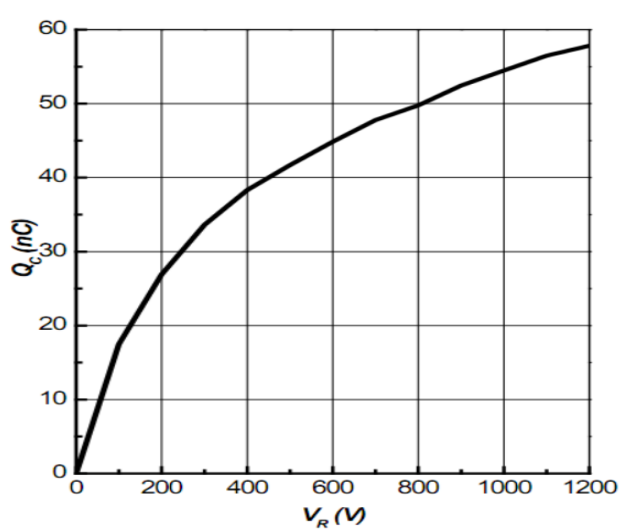


Figure 4. Total Capacitive Charge vs. Reverse Voltage

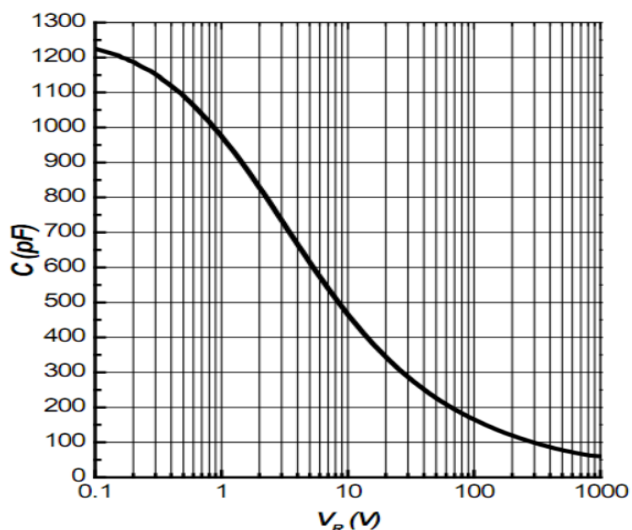


Figure 5. Total Capacitance vs. Reverse Voltage

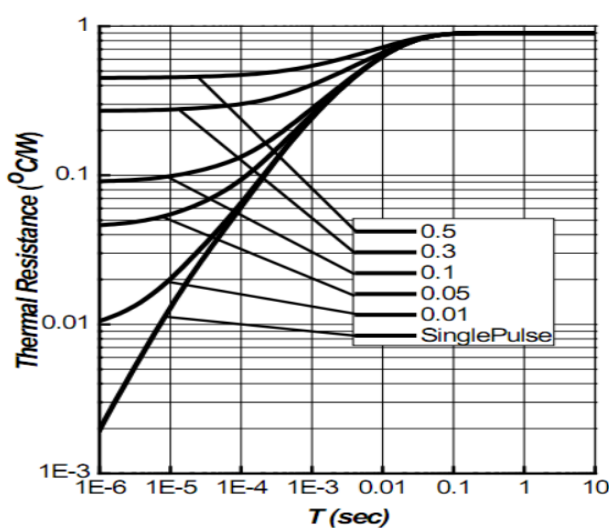
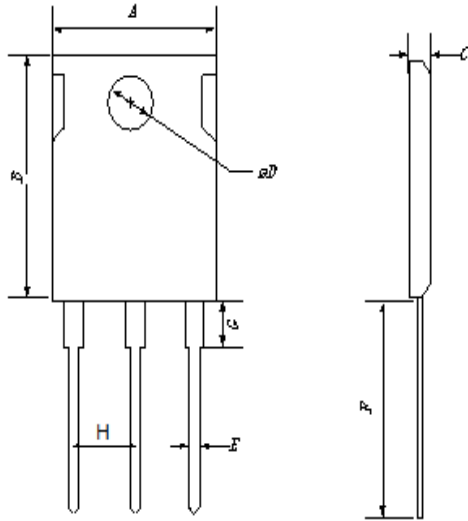


Figure 6. Transient Thermal Impedance

Package Dimensions

Package TO-247-3



Symbol	Min. (mm)	Typ. (mm)	Max. (mm)
A	14.18	15.75	17.33
B	18.45	20.5	22.55
C	4.50	5.00	5.50
D	3.15	3.50	3.85
E	1.08	1.20	1.32
F	18.27	20.30	22.33
G	4.21	4.68	5.15
H	4.91	5.46	6.01